

Appl. No. 09/464,297
Amendment dated January 22, 2004
Reply to Office Action of October 22, 2003

Docket No. 99-039/RCE

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: : Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball, Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

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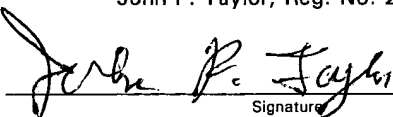
Filed: : December 15, 1999

Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U. : 1765

Examiner : Lan Vinh

Docket No. : 99-039/RCE

CERTIFICATE OF MAILING	
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	 Signature
	January 22, 2004 Date of Signature

AMENDMENT

Honorable Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

Date: January 22, 2004

Sir:

This is in response to the Sixth Office Action mailed October 22, 2003.